ON Semiconductor®

FDMC4435BZ

P-Channel Power Trench® MOSFET

-30 V, -18 A, 20 mΩ

Features

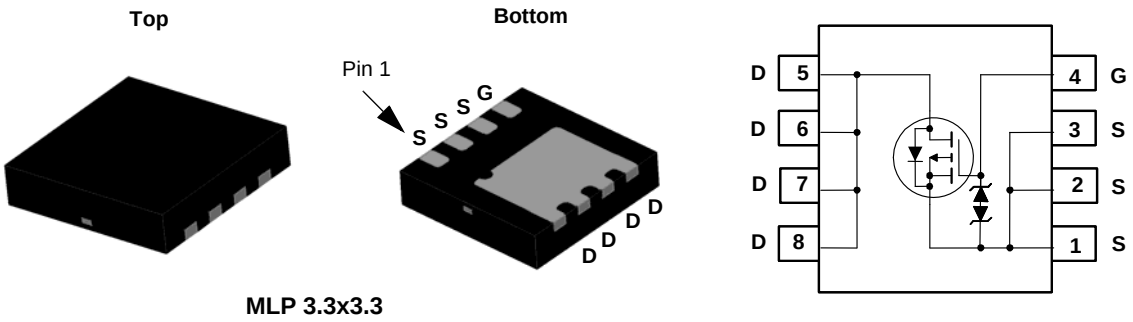
- Max $r_{DS(on)}$ = 20 mΩ at V_{GS} = -10 V, I_D = -8.5 A
- Max $r_{DS(on)}$ = 37 mΩ at V_{GS} = -4.5 V, I_D = -6.3 A
- Extended V_{GSS} range (-25 V) for battery applications
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability
- HBM ESD protection level >7 kV typical (Note 4)
- 100% UIL Tested
- Termination is Lead-free and RoHS Compliant

General Description

This P-Channel MOSFET is produced using ON Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Applications

- High side in DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook



MLP 3.3x3.3

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			-30	V
V_{GS}	Gate to Source Voltage			±25	V
I_D	Drain Current -Continuous	T_C = 25 °C		-18	A
	-Continuous	T_A = 25 °C	(Note 1a)	-8.5	
	-Pulsed			-50	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	32	mJ
P_D	Power Dissipation	T_C = 25 °C		31	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC4435BZ	FDMC4435BZ	MLP 3.3X3.3	13 ''	12 mm	3000 units

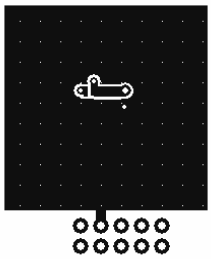
©2010 Semiconductor Components Industries, LLC.

Electrical Characteristics T_J = 25 °C unless otherwise noted

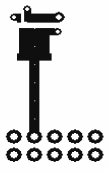
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = -250 μA, V_{GS} = 0 V	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, referenced to 25 °C		21		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -24 V, V_{GS} = 0 V,			-1	μA
		T_J = 125 °C			-100	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±25 V, V_{DS} = 0 V			±10	μA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = -250 μA	-1.0	-1.8	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μA, referenced to 25 °C		-5		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = -10 V, I_D = -8.5 A		14	20	mΩ
		V_{GS} = -4.5 V, I_D = -6.3 A		21	37	
		V_{GS} = -10 V, I_D = -8.5 A, T_J = 125 °C		20	29	
g_{FS}	Forward Transconductance	V_{DD} = -5 V, I_D = -8.5 A		25		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz		1535	2040	pF
C_{oss}	Output Capacitance			310	410	pF
C_{rss}	Reverse Transfer Capacitance			280	420	pF
R_g	Gate Resistance	f = 1 MHz		4		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -15 V, I_D = -8.5 A, V_{GS} = -10 V, R_{GEN} = 6 Ω		10	20	ns
t_r	Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			35	56	ns
t_f	Fall Time			19	34	ns
Q_g	Total Gate Charge	V_{GS}=0V to -10V, V_{DD} = -15 V, I_D = -8.5 A		38	53	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to -4.5 V, V_{DD} = -15 V, I_D = -8.5 A		20	28	nC
Q_{gs}	Gate to Source Charge	V_{DD} = -15 V, I_D = -8.5 A		4.3		nC
Q_{gd}	Gate to Drain “Miller” Charge			11		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = -8.5A (Note 2)		0.86	1.5	V
		V_{GS} = 0 V, I_S = -1.9 A (Note 2)		0.74	1.2	
t_{rr}	Reverse Recovery Time	I_F = -8.5 A, di/dt = 100 A/μs		26	40	ns
Q_{rr}	Reverse Recovery Charge			12	20	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.

3. Starting T_J = 25°C; P-ch: L = 1mH, I_{AS} = -8A, V_{DD} = -27V, V_{GS} = -10V.

4. The diode connected between the gate and source servers only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25°C unless otherwise noted

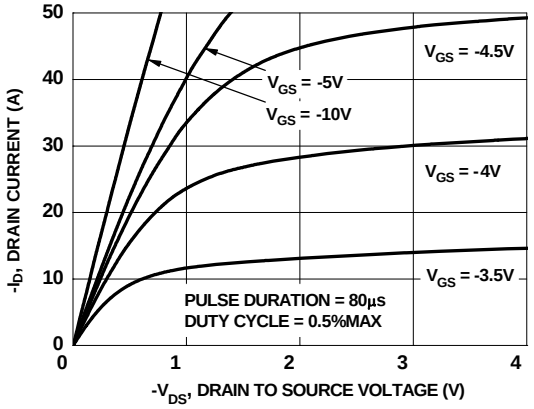


Figure 1. On-Region Characteristics

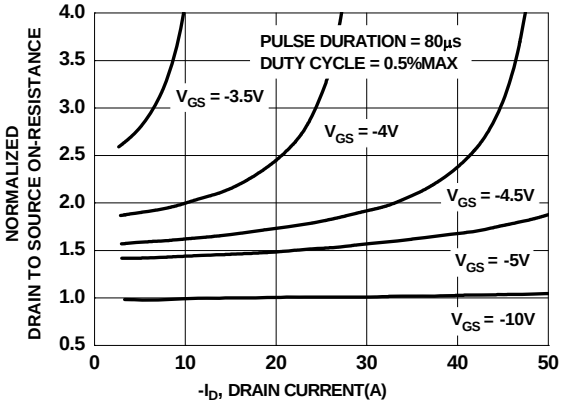


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

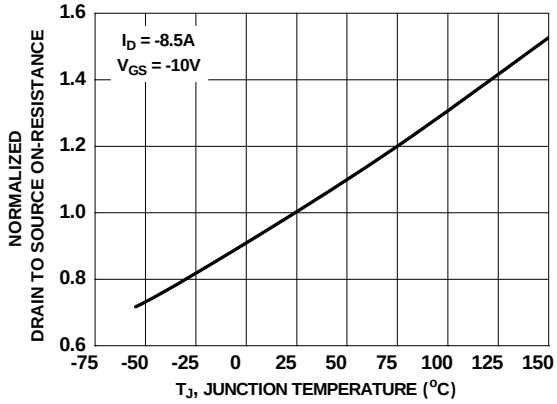


Figure 3. Normalized On-Resistance vs Junction Temperature

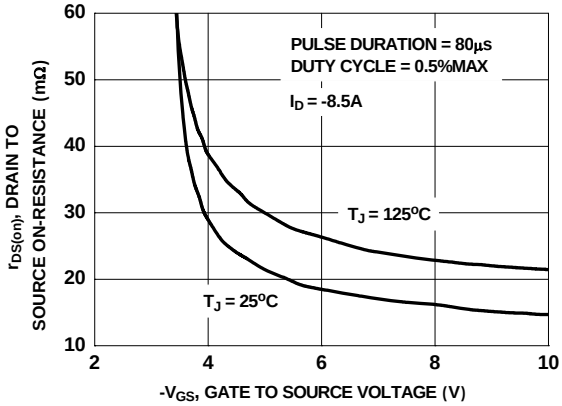


Figure 4. On-Resistance vs Gate to Source Voltage

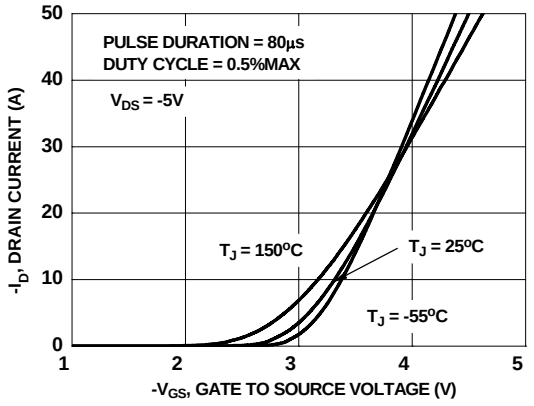


Figure 5. Transfer Characteristics

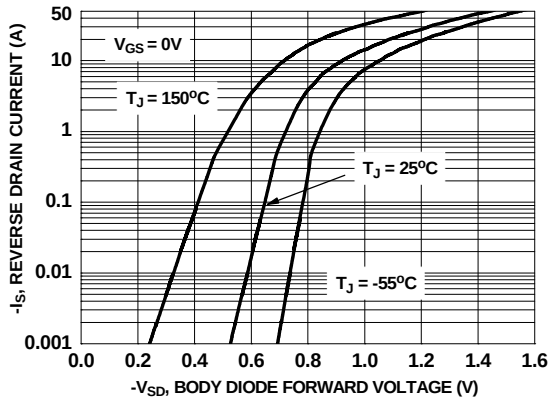


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

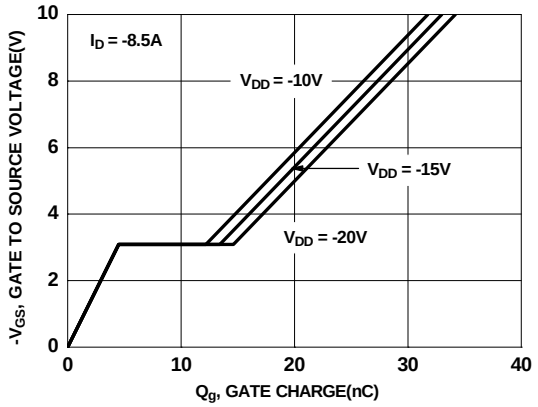


Figure 7. Gate Charge Characteristics

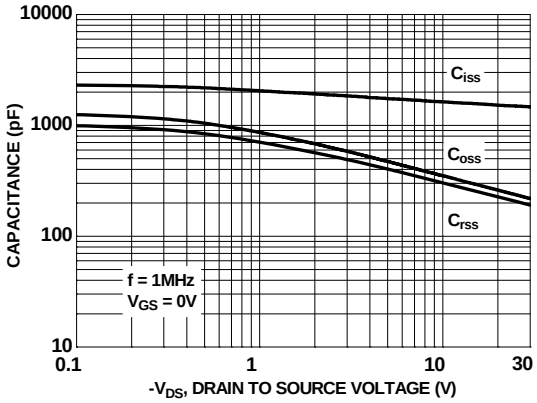


Figure 8. Capacitance vs Drain to Source Voltage

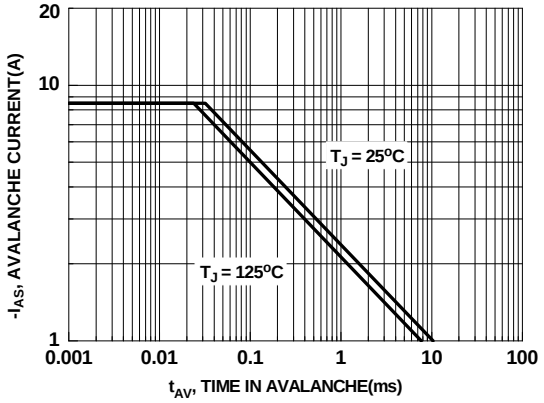


Figure 9. Unclamped Inductive Switching Capability

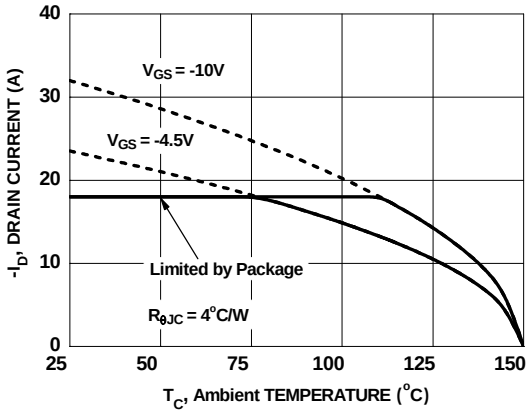


Figure 10. Maximum Continuous Drain Current vs Case Temperature

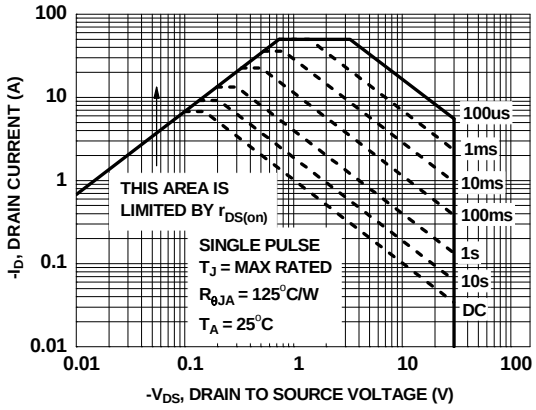


Figure 11. Forward Bias Safe Operating Area

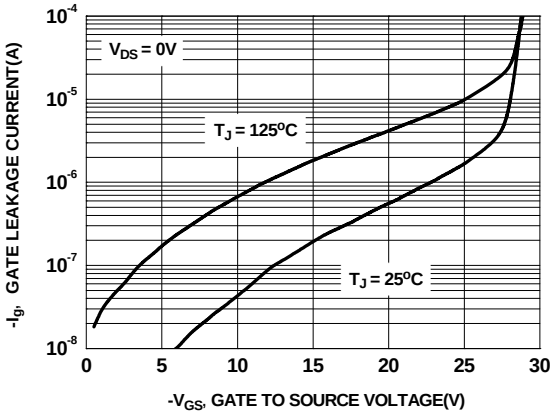


Figure 12. Igss vs Vgss

Typical Characteristics T_J = 25°C unless otherwise noted

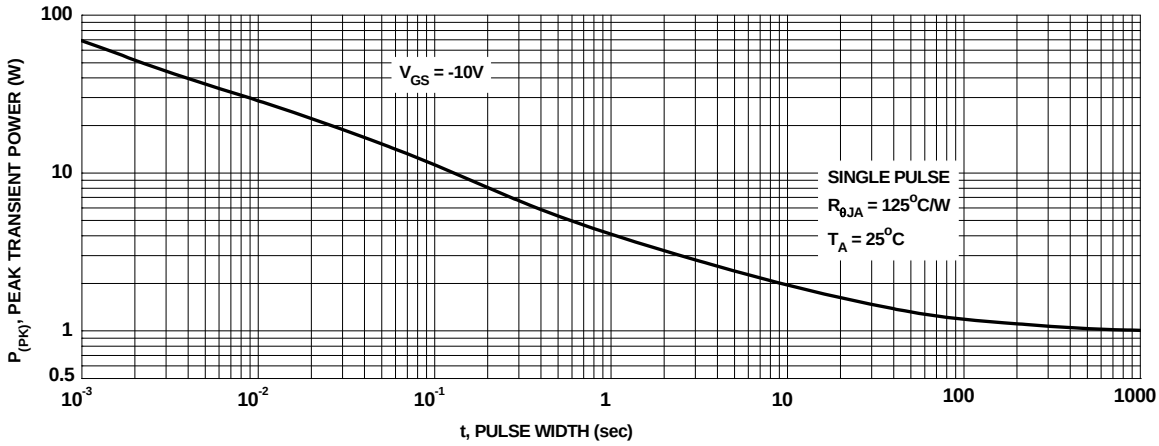


Figure 13. Single Pulse Maximum Power Dissipation

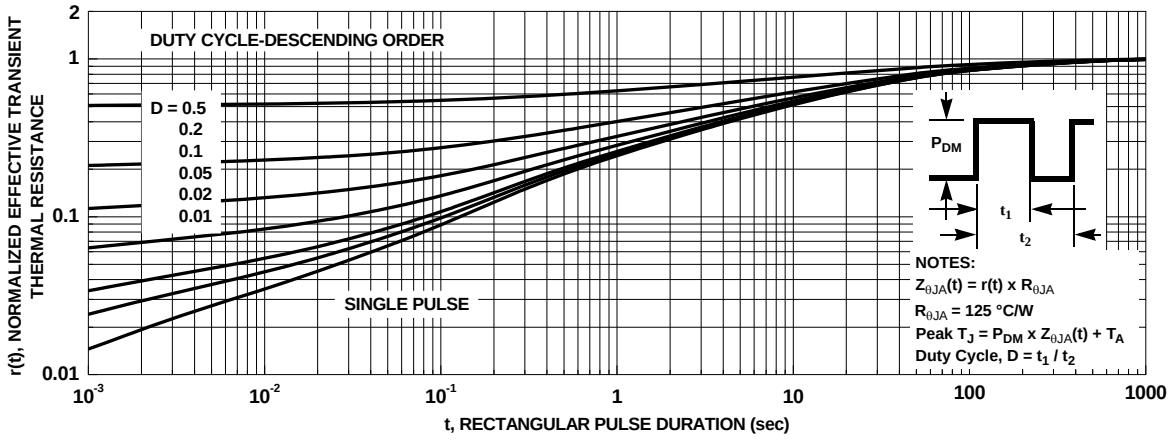
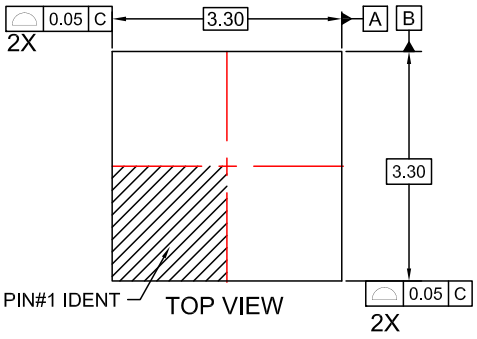
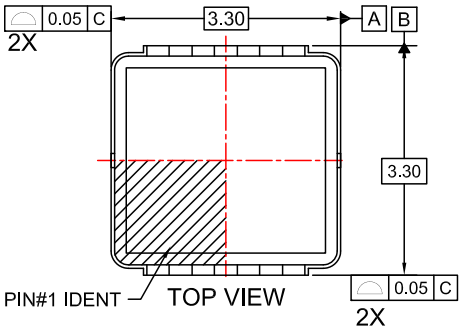
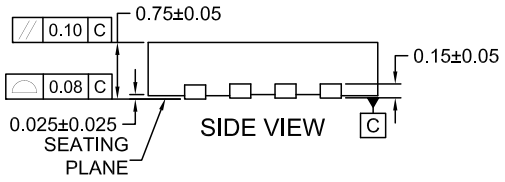


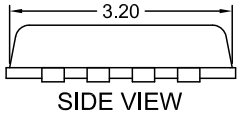
Figure 14. Transient Thermal Response Curve

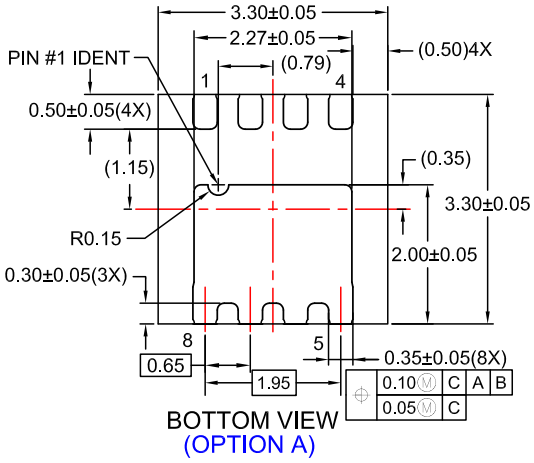
Dimensional Outline and Pad Layout

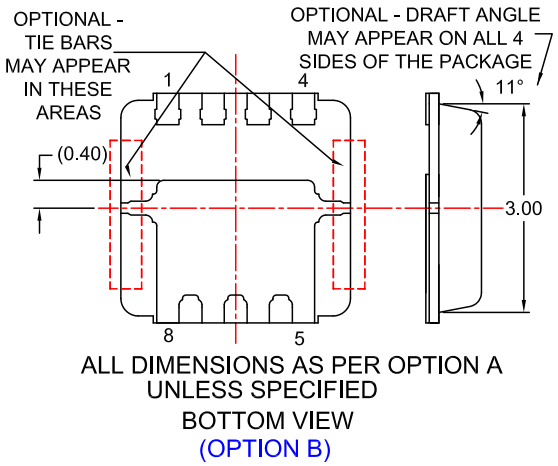


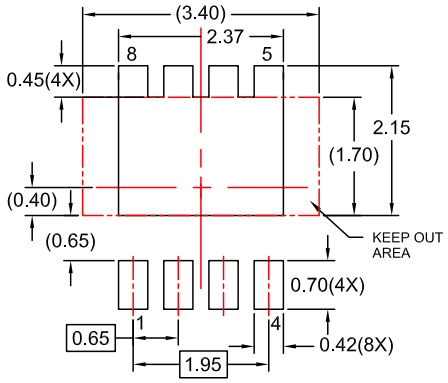




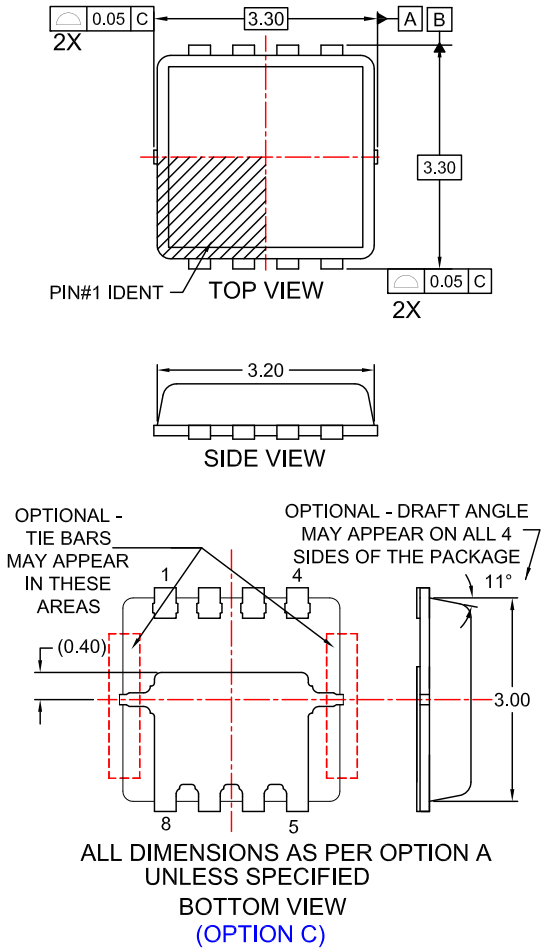








Dimensional Outline and Pad Layout



NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN
E. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
F. DRAWING FILENAME: MKT-MLP08Wrev3.
G. OPTION A - SAWN MLP, OPTIONS B & C - PUNCH MLP.

Package drawings are provided as a service to customers considering ON Semiconductor components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a ON Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of ON Semiconductor's worldwide terms and conditions, specifically the warranty therein, which covers ON Semiconductor products.

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

FDMC4435BZ FDMC4435BZ-F126 FDMC4435BZ-F127